

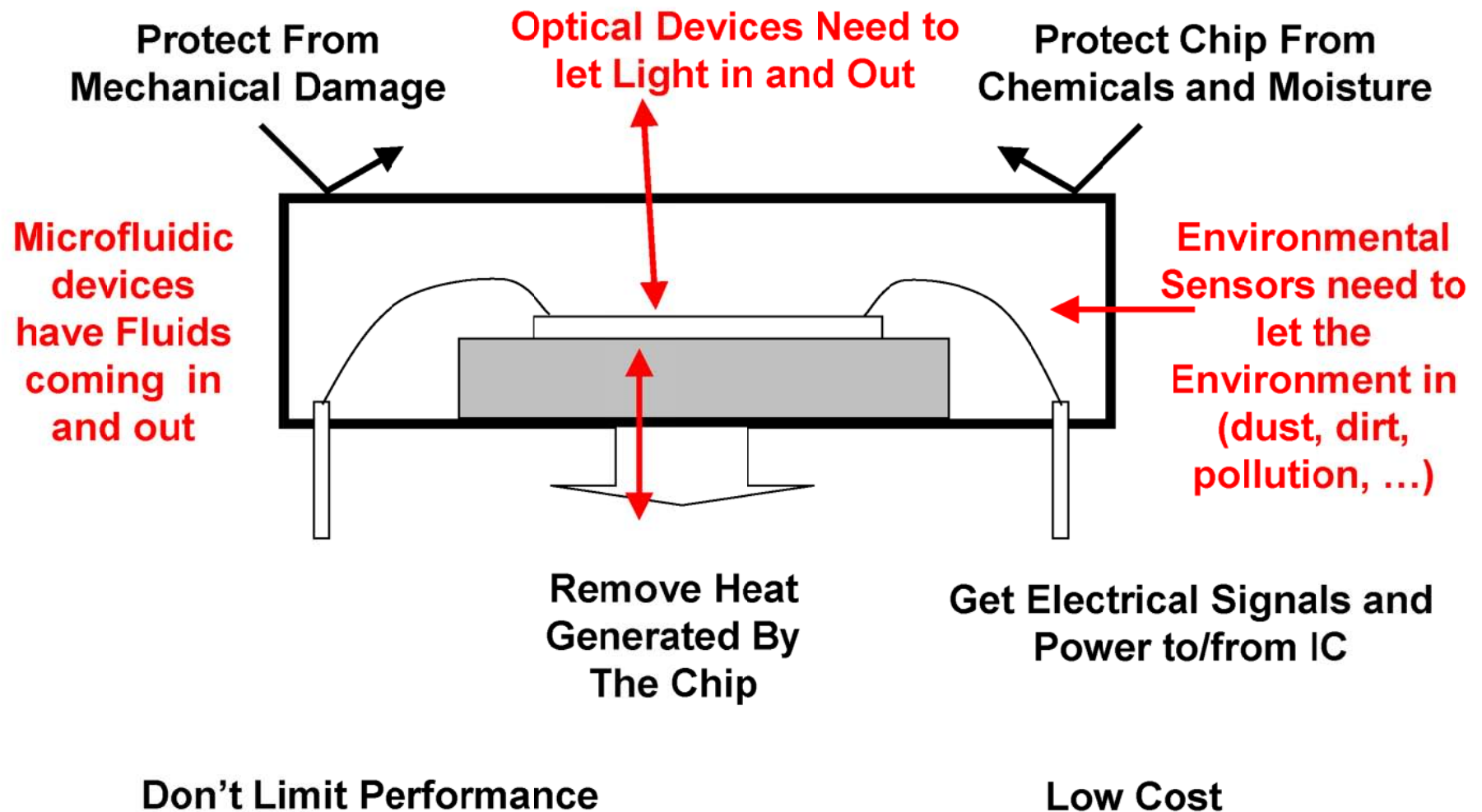


MEMS PACKAGING

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GOAL OF MEMS PACKAGING





LAST YEAR

- **Some of you heard me talk last year**
- **This talk is intended to be complementary to last years talk**
- **It covers MEMS packaging techniques that are not used by the integrated circuit industry**



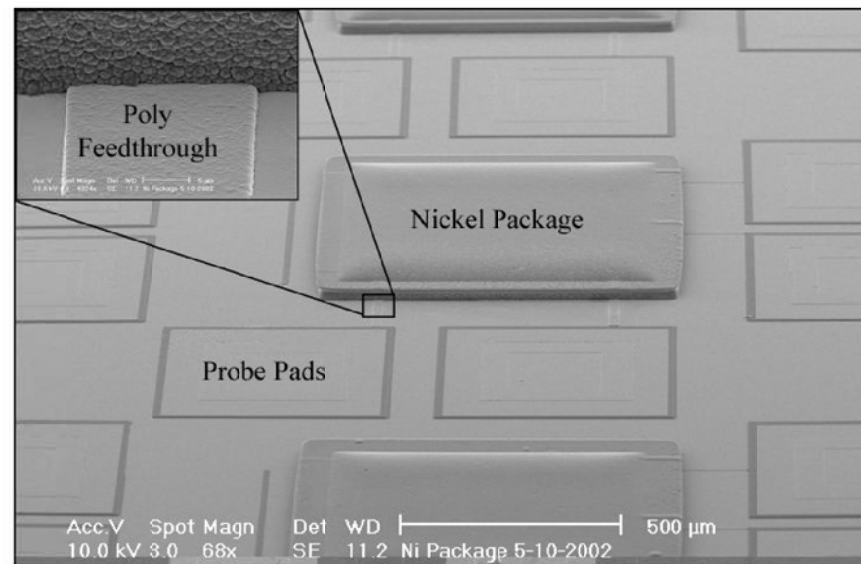
OUTLINE

- **Integrated Package**
- **Wafer Bonding**
 - Fusion
 - Anodic
 - Glass frit
 - Thermocompression
 - Solder
- **MEMS Packaging Issues**



INTEGRATED PACKAGES

- Formed during the fabrication process
- Using fabrication equipment (evaporators, LPCVD furnaces, lithography etc.)
- Not formed by using assembly techniques



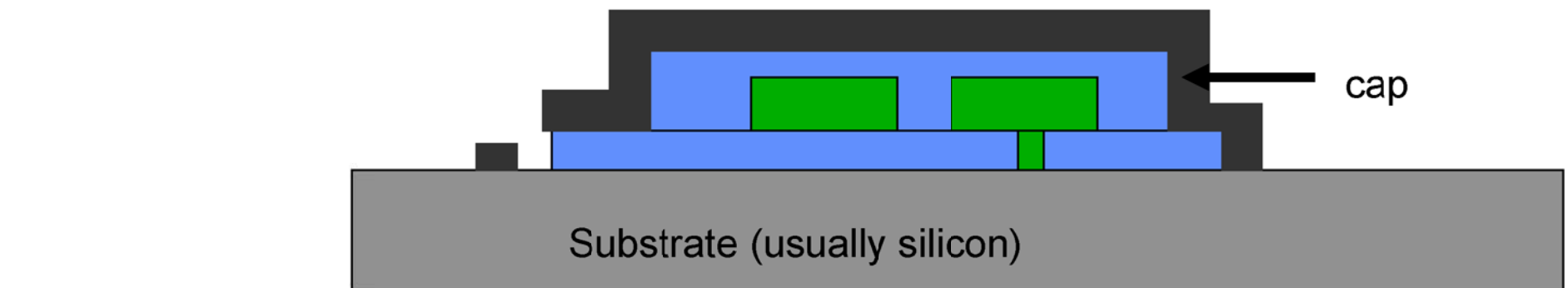
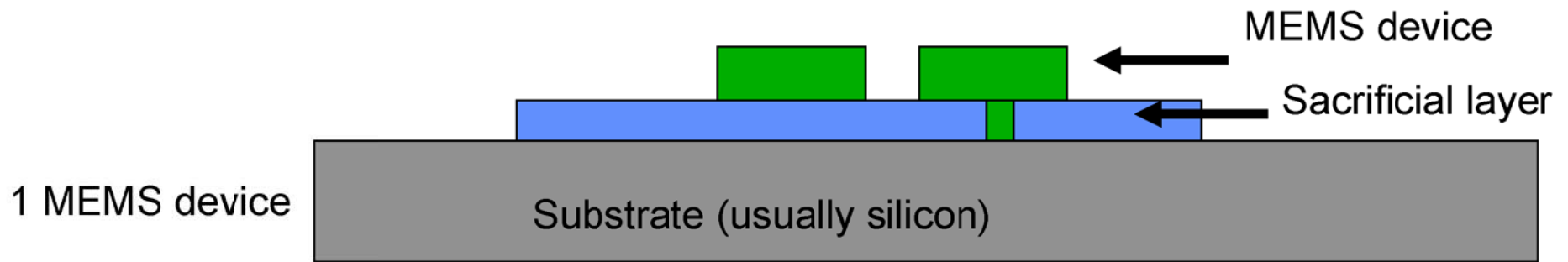


INTEGRATED PACKAGE

- **Protected volume (package?) is formed during the fabrication process**
- **Step 1: The MEMS device (generally a surface micromachine) is fabricated**
- **Step 2: A cap or cover and sacrificial layer is formed over the MEMS device**
- **Step 3: The MEMS device is released (sacrificial layer removed) through a hole in the cover**
- **Step 4: The hole in the cover is sealed**



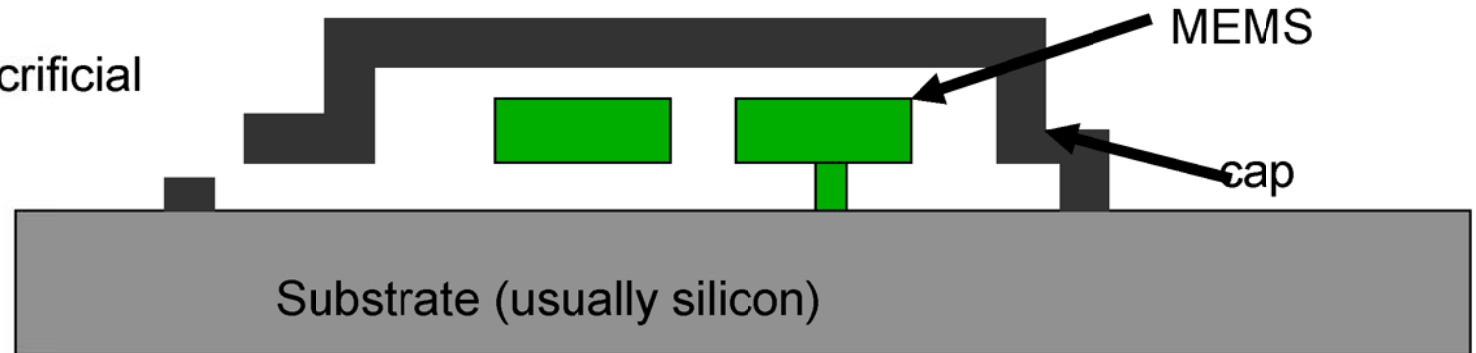
INTEGRATED PACKAGE (SIDE VIEW)





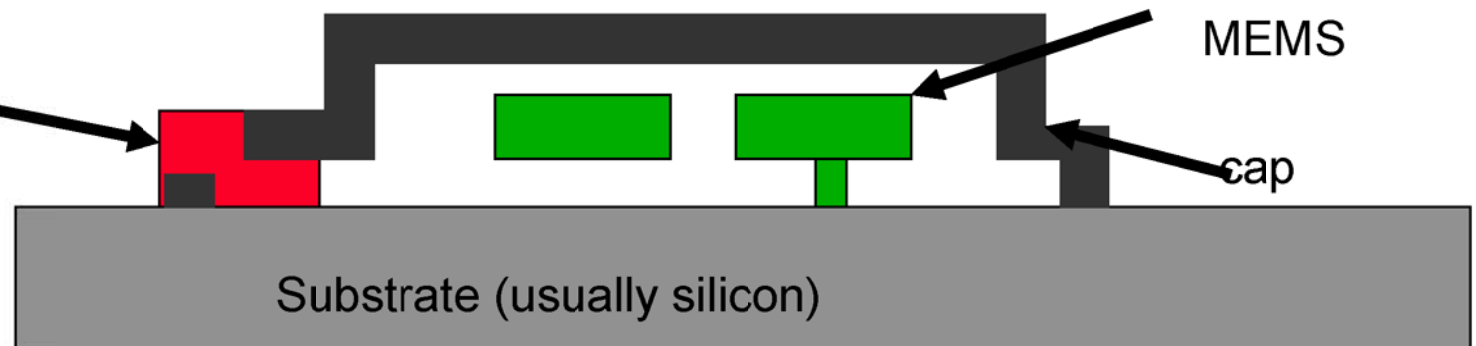
INTEGRATED PACKAGE

3 Removal of sacrificial layer



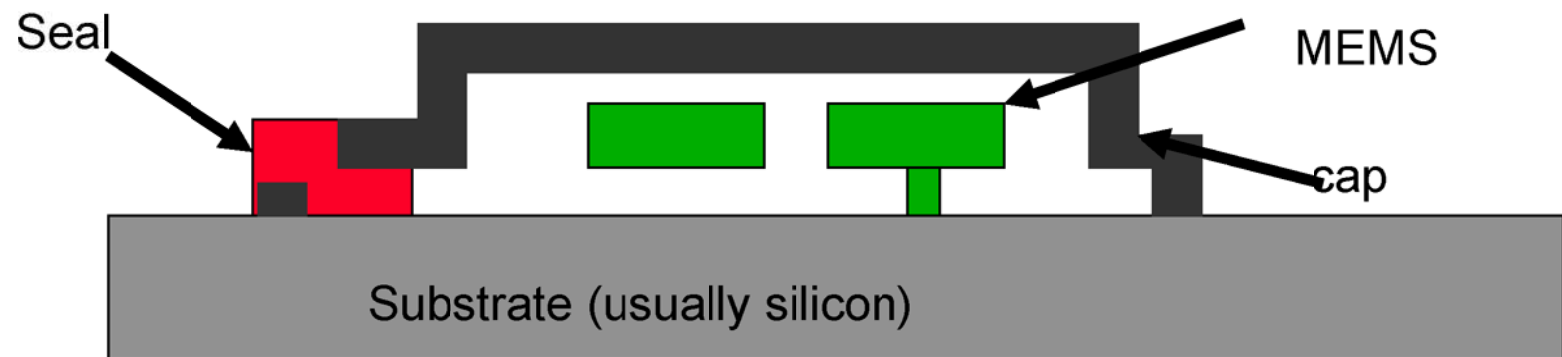
Seal

4 Cap is sealed





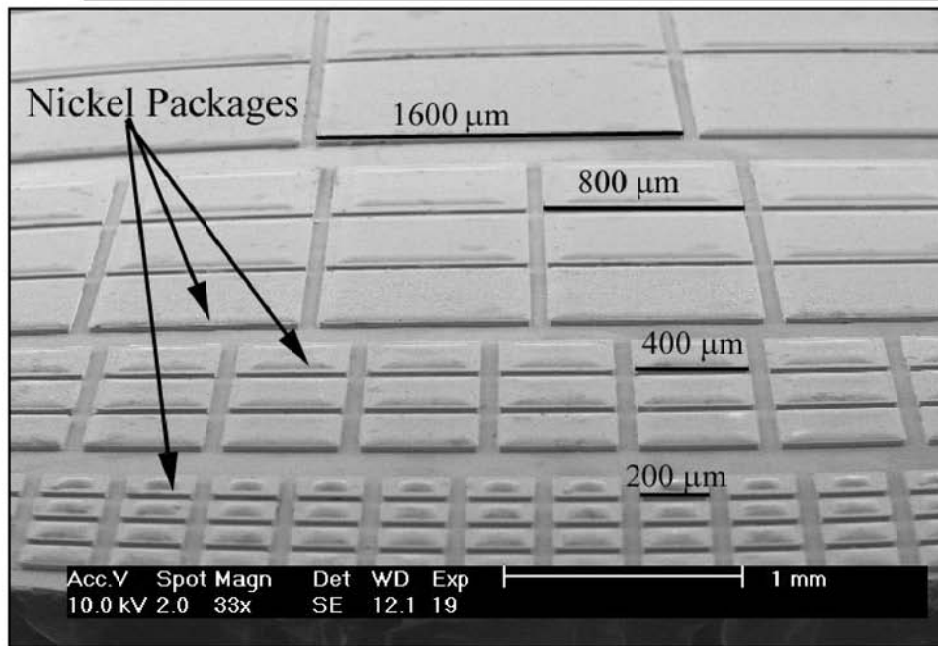
INTEGRATED PACKAGE



- **Materials used in integrated packages**
 - Polysilicon lids and MEMS, silicon dioxide sacrificial layer, sealed in LPCVD furnace
 - Silicon nitride lid and polysilicon MEMS, silicon dioxide sacrificial layer sealed in LPCVD furnace
 - Permeable polysilicon lid (no hole to seal)
 - Aluminum or other metal has been evaporated or sputtered to seal the hole in the cover

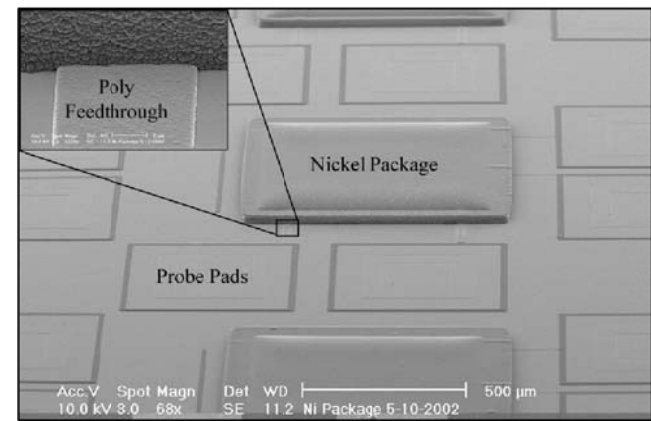


INTEGRATED MEMS PACKAGE

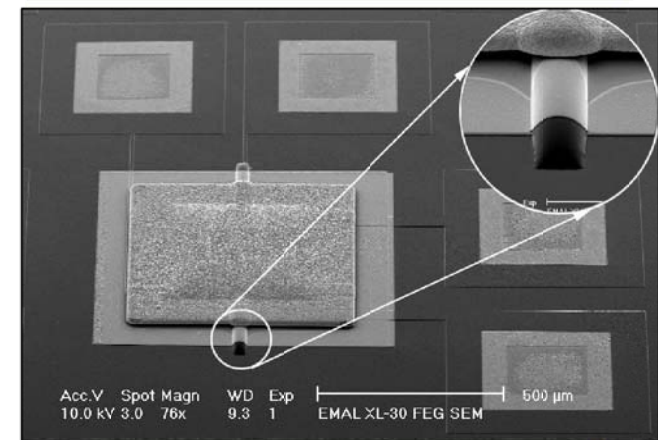


Electroplated nickel packages prior to sealing – note the variety of geometries possible

800 μm X800 μm package takes~2.5 hours to clean and release



Electrical Feedthroughs



Fluidic Access Port

Brian Stark, U of Michigan



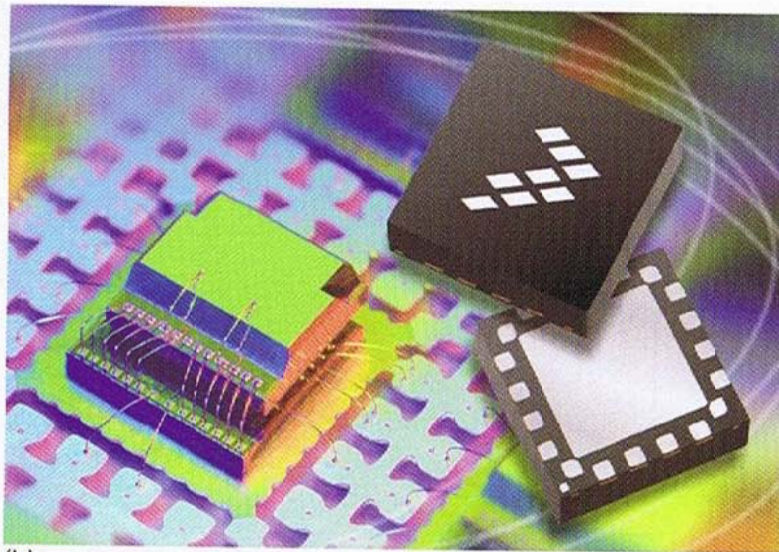
OUTLINE

- Integrated Package
- **Wafer Bonding**
 - Fusion
 - Anodic
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 - Thermocompression
 - Solder
- MEMS packaging issues



WAFER BONDING

- Wafer bonding is a process that has been compared to alchemy
- Very dependent on surface finish and surface conditions (cleaning)
- In principle (not in practice), almost any materials can be bonded together if the surfaces are flat and clean enough and if the van der Waals forces are strong enough
- Bonding forces include van der Waals (dipole), capillary (water), and electrostatic. These then can lead to covalent bond



- Wafer bonding provides a cover that protects the MEMS device
- This process is often used in high volume manufacturing

Devices from Freescale Semiconductor
MEMS: Applications M. Gad-el_Had ed.



Sandia
National
Laboratories



WAFER BONDING CONSIDERATIONS

- **Particle/defect coverage**
- **Wafer warpage**
- **How to get lines out**
- **Temperature**
- **Force**
- **Processing considerations**
- **Types of wafers used**



OVERVIEW OF BONDING METHODS

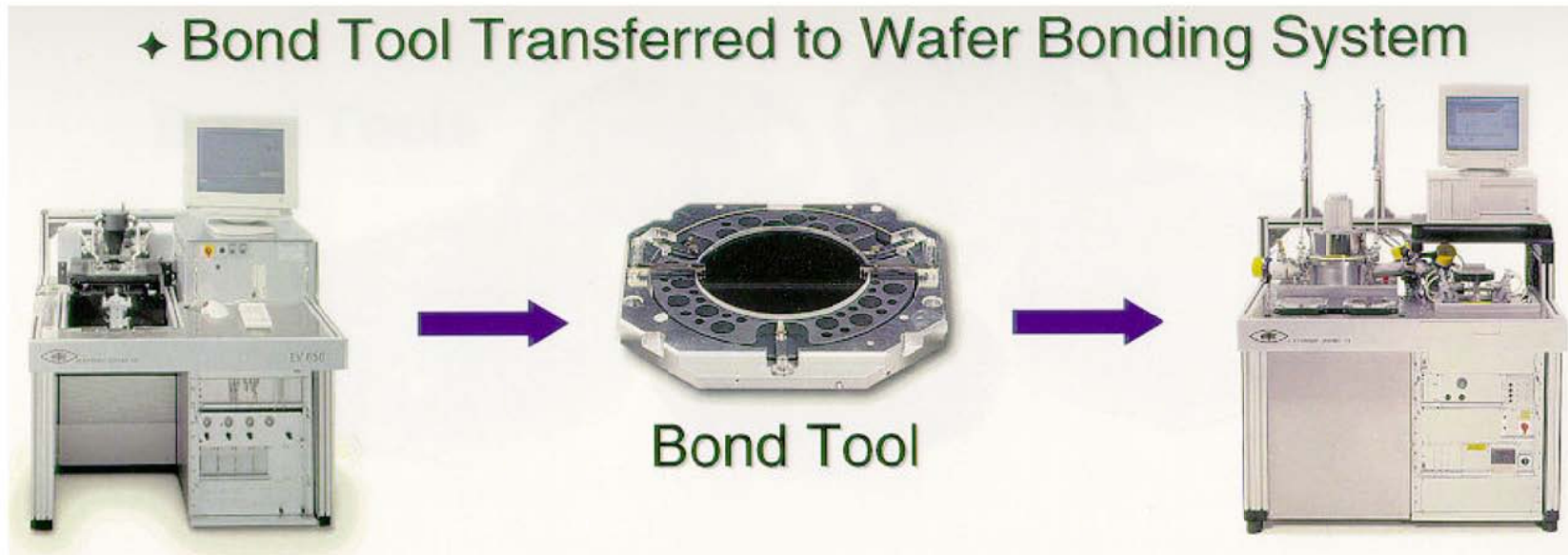
Bonding Method	Temperature	Hermeticity
Epoxy	Low	No
Eutectic	Medium	Yes
Anodic	Medium	Yes
Fusion	Very High	Yes
Integrated Process	High	Yes



BONDING EQUIPMENT

- 2 processes
 - Alignment of the wafers
 - Bonding of the wafers together
- Wafer Aligner: Positions ($\pm 2\mu\text{m}$) up to 3 Wafers Together In a Transport Fixture for Bonding
- Bonder: Accepts Fixture and Bonds Wafers Using Heat, Pressure, or Voltage
- Bonding Methods: Anodic bonding; Silicon Direct; Epoxy; Glass Frit; Thermocompression; Solder

♦ Bond Tool Transferred to Wafer Bonding System





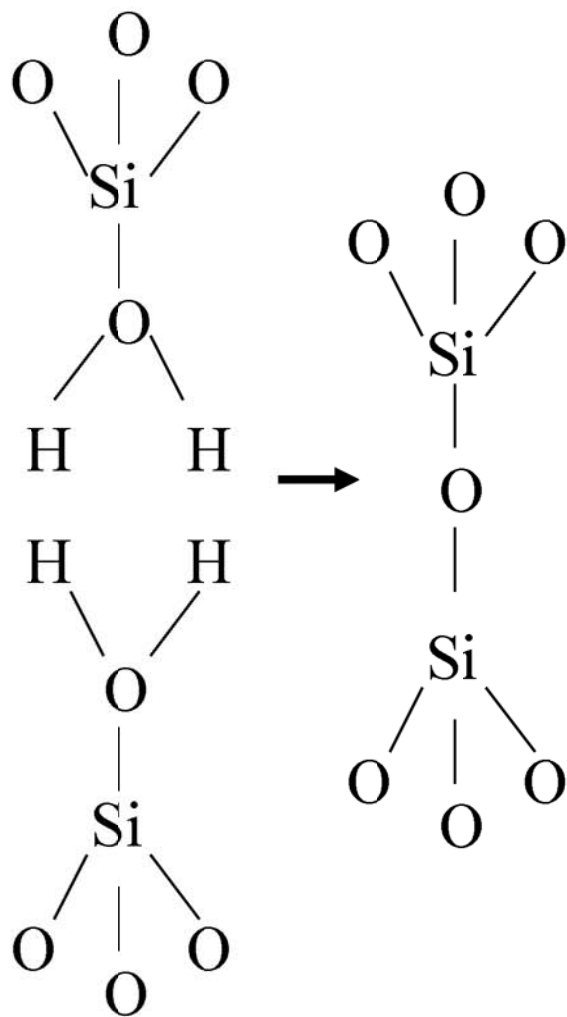
FUSION BONDING

-
- Needs very smooth surfaces (5Å roughness) NO PARTICLES
 - Hydrophilic or hydrophobic surfaces (surface preparation VERY important)
 - Hydrophilic via boiling nitric acid dip, $\text{H}_2\text{O}_2:\text{H}_2\text{SO}_4$, and/or O_2 plasma
 - Hydrophobic via RCA clean and HF dip (less common)
 - Both surfaces are brought into contact at room temperature, and then annealed at 800-1100 C
 - Bond strengths about 10-20 MPa
 - Besides MEMS applications include
 - Silicon on Insulator (SOI)
 - Replacement for epitaxy (bonding instead of growing)

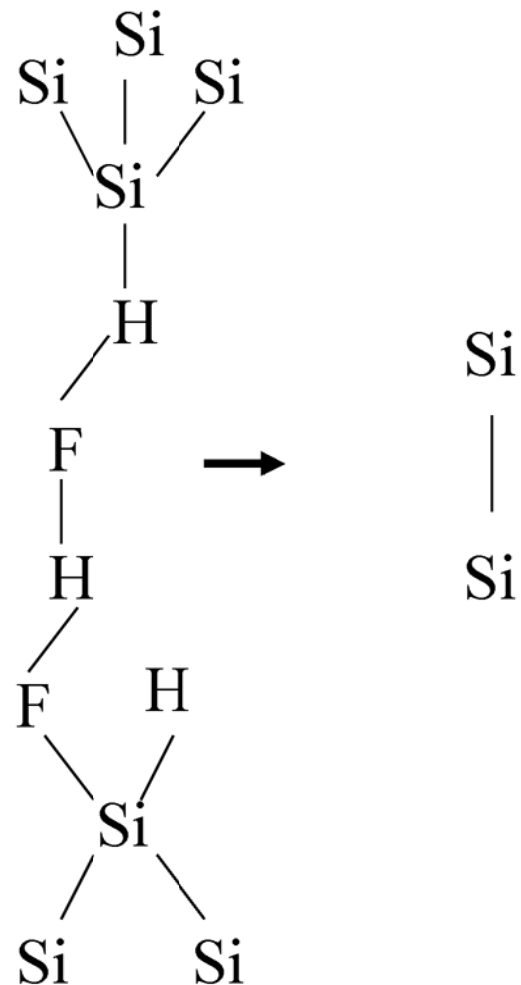


BONDING MECHANISMS FOR HYDROPHILLIC AND HYDROPHOBIC SILICON

HYDROPHILLIC

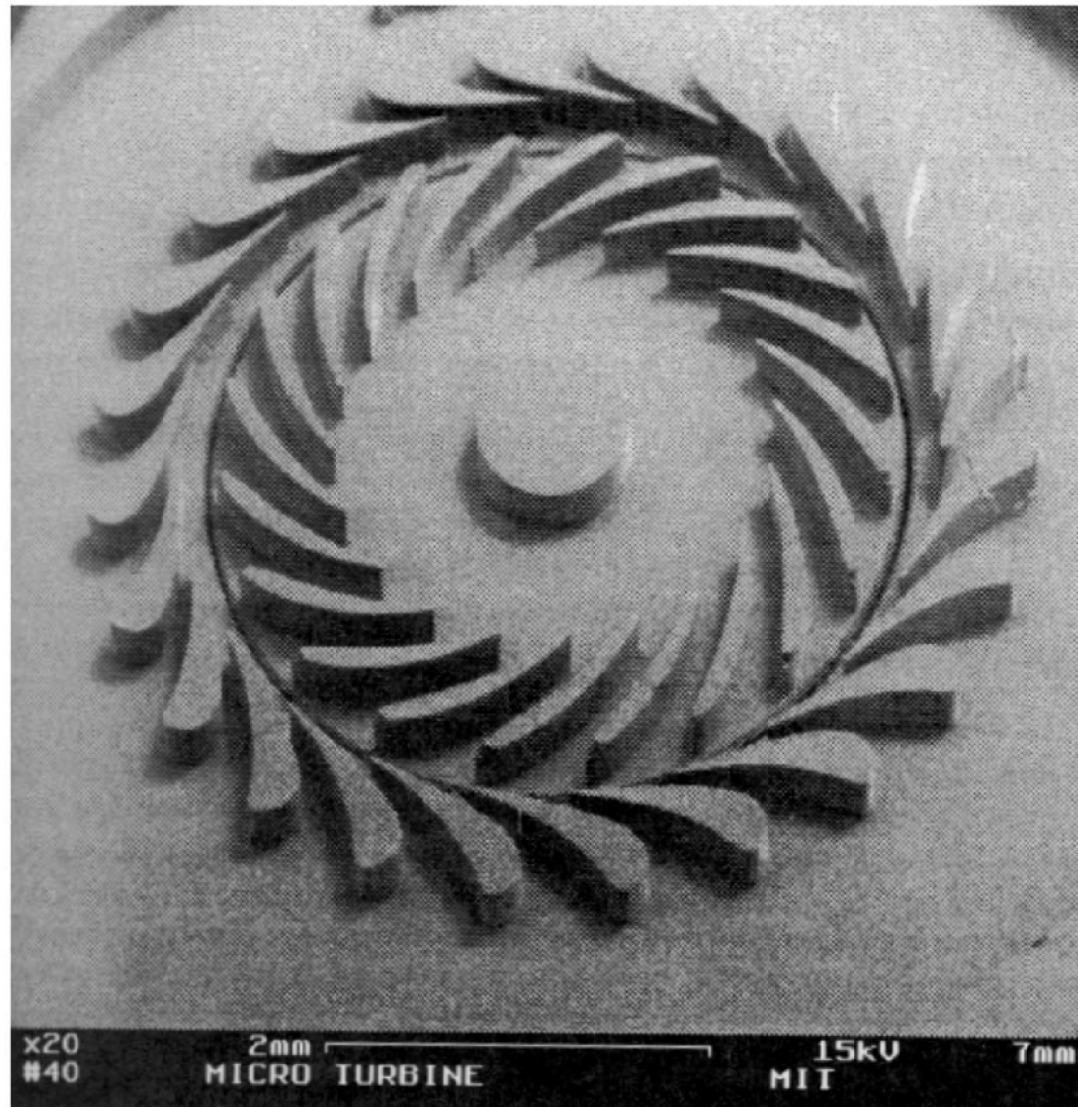


HYDROPHOBIC





MIT FUSION BONDED μ TURBINE





PLASMA ACTIVATED BONDING

- **Plasma activated bonding can reduce the temperature required for fusion bonding to room temperature**
- **However, the surfaces must be extremely flat and clean**
- **See Suss Microtec and Ziptronix among others for more information www.suss.com
www.ziptronix.com**

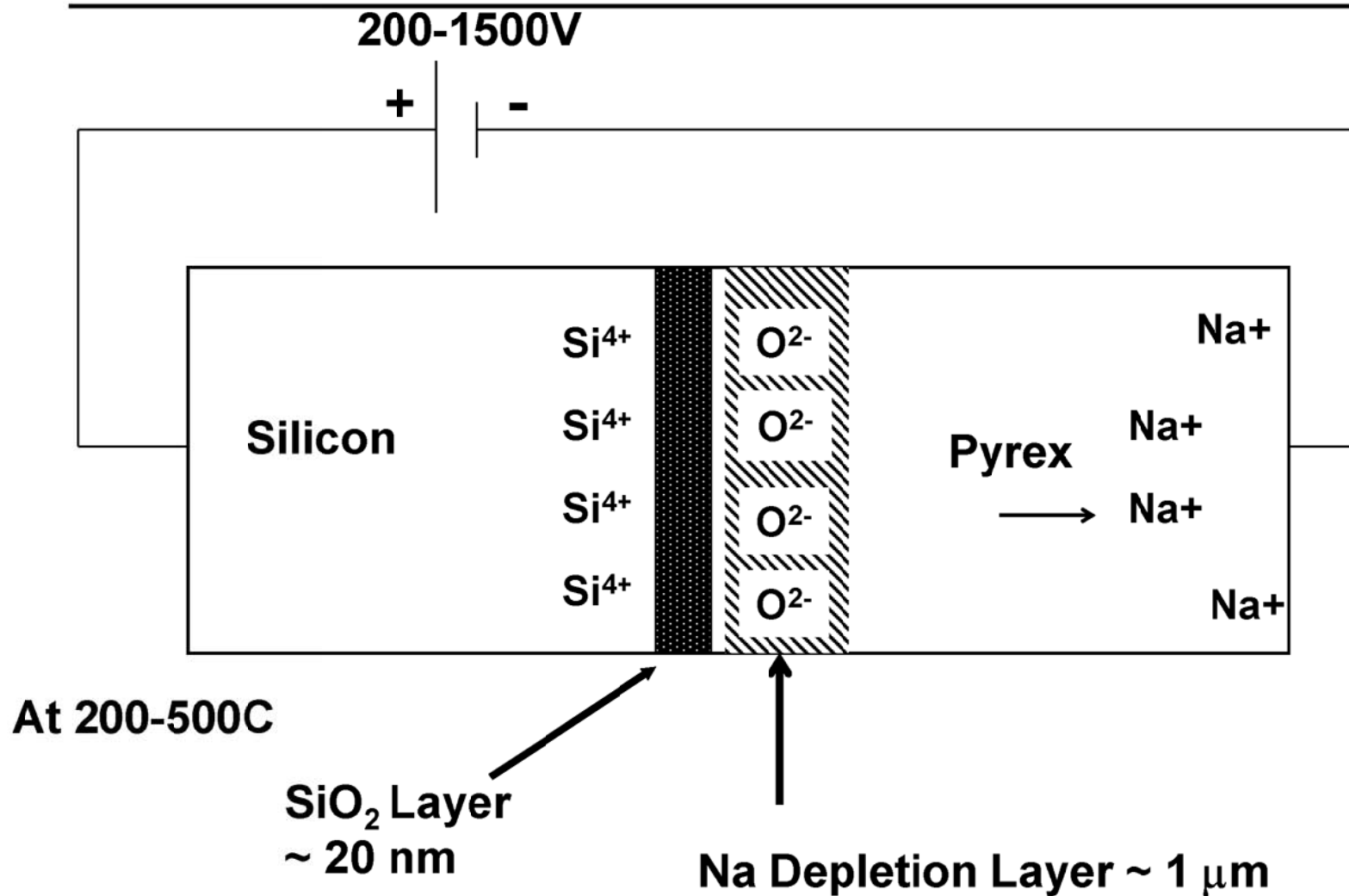


ANODIC (ELECTROSTATIC) BONDING

- Is done at lower temperatures than fusion bonding 200-500C
- Will only work between selected materials (Al, W, Si₃N₄, Cr, Ti, SiO₂, Si, and glass with mobile ions)
- Glass used is typically borosilicate pyrex (Corning 7740) but some other glasses will work
- Depending on temperature and voltage will bond over rougher surfaces than fusion bonding (between 50 nm and 1 μ m)
- You can bond over feedthroughs, steps and particles
- Silicon and pyrex have closely matched TCEs

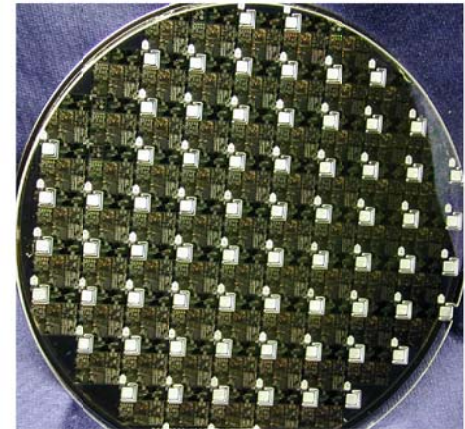
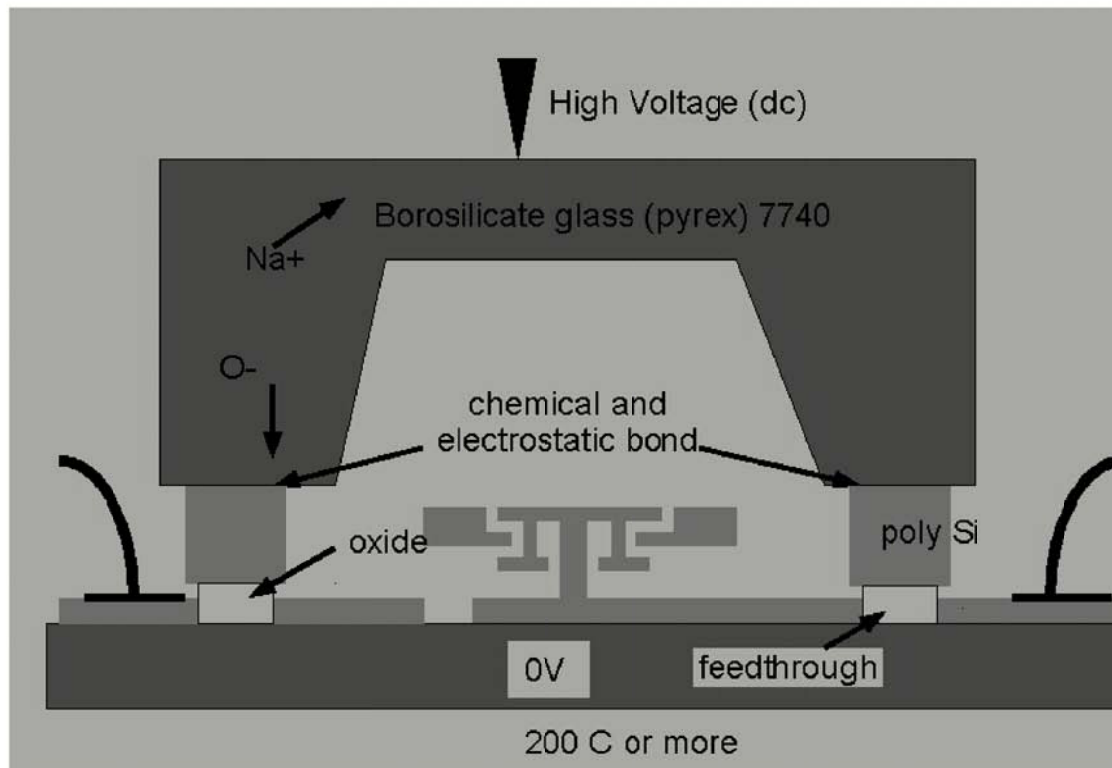


ANODIC BONDING MECHANISM





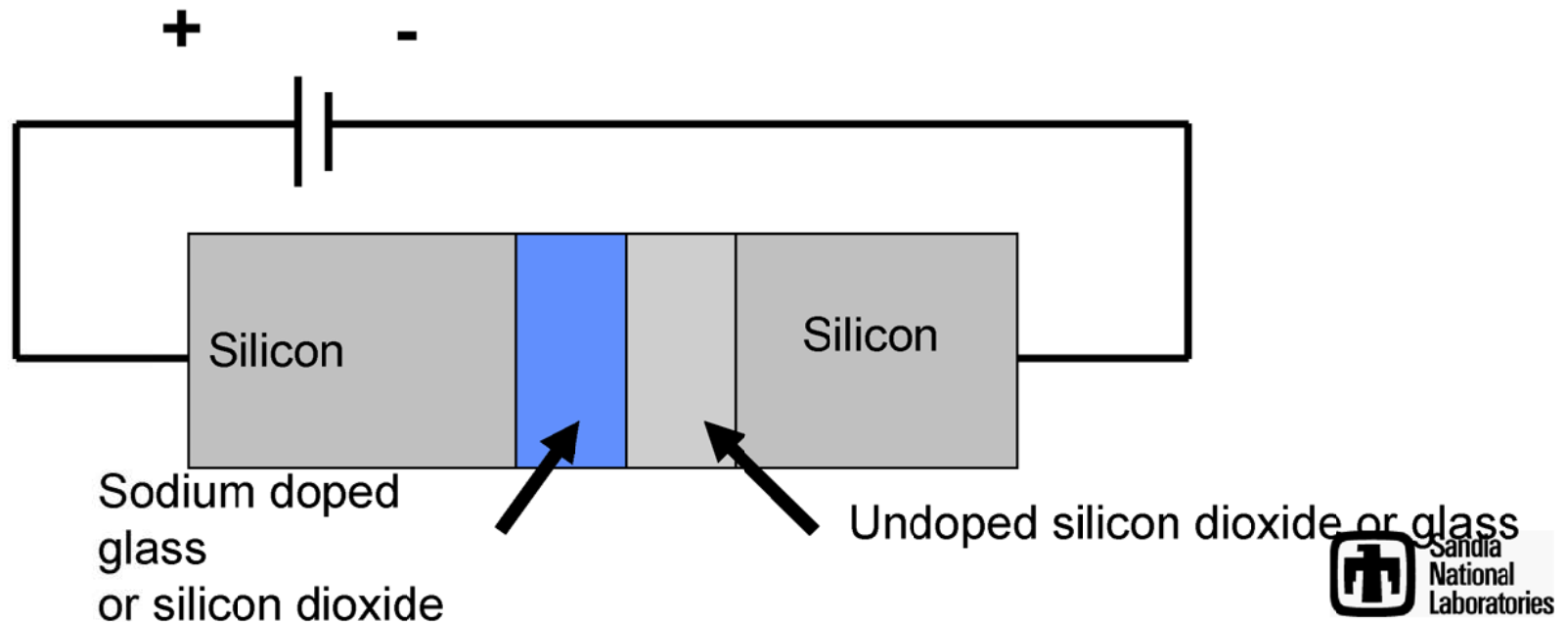
SURFACE MICROMACHINE WAFER LEVEL PACKAGING





ANODIC BONDING WITH THIN FILMS

- Thin films of either silicon dioxide or glass doped with sodium
- Can be used to bond silicon to silicon or other non glass substrates
- Uses a higher temperature and longer bonding time than regular anodic bonding



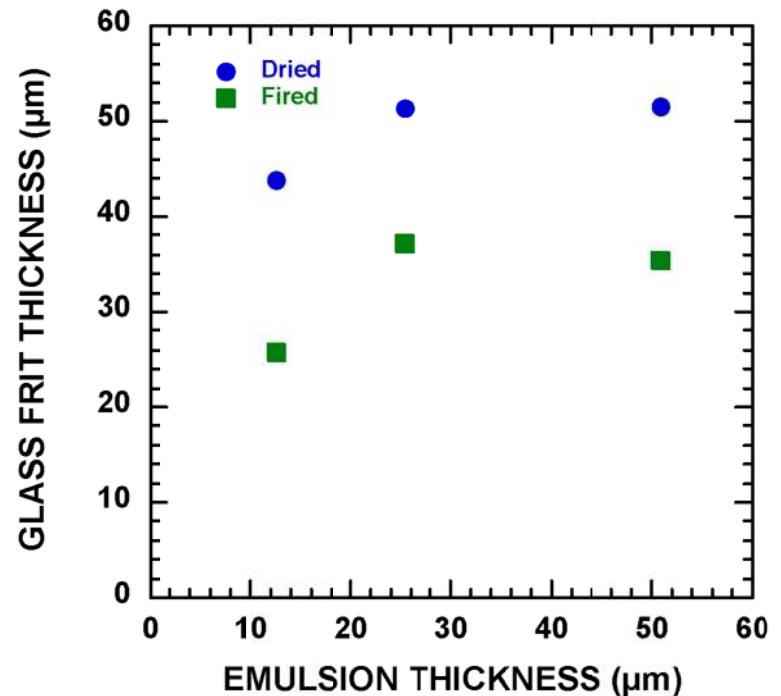
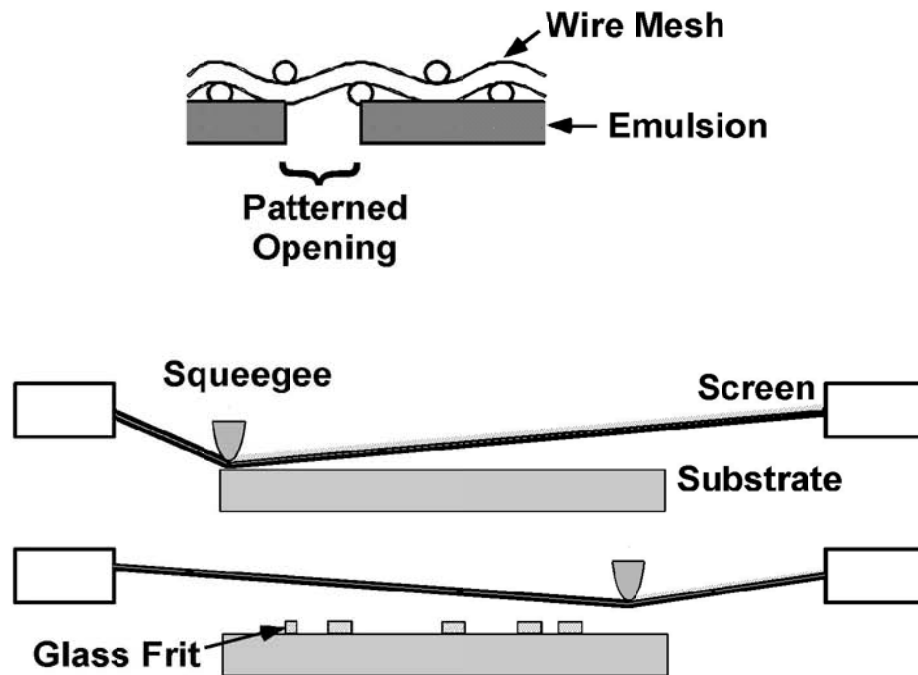


GLASS FRIT

- **Does not use high voltages**
- **Uses moderate temperatures**
- **Will not short out metallic signal lines**
- **Robust and reliable bonding technique**
- **Limited requirement for planarity because the glass frit will deform**



GLASS FRIT SCREEN PRINTING

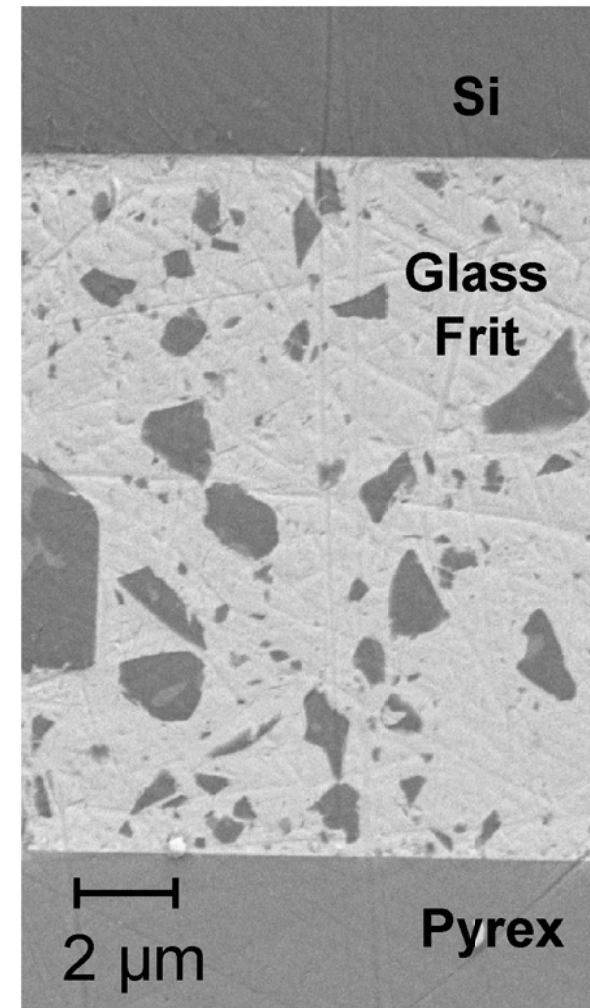
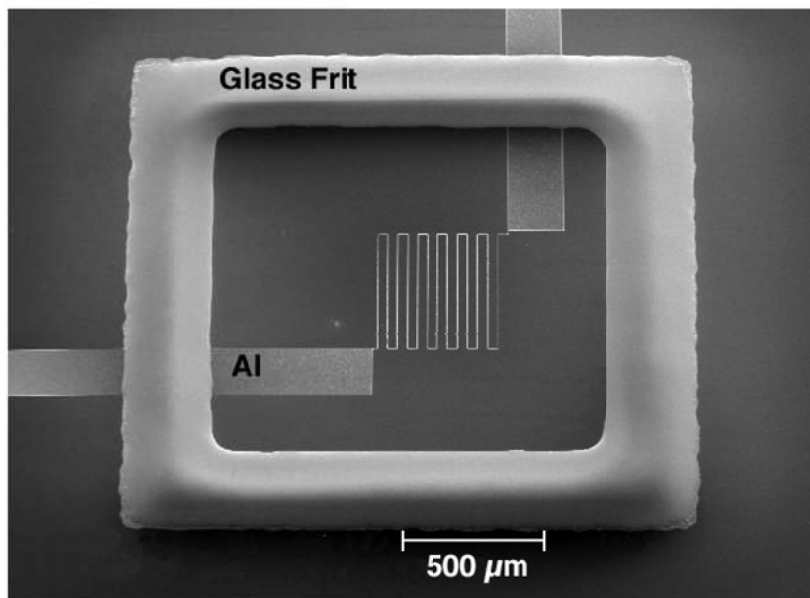


- Photopatterned Screen for Bond Ring Patterning: No Lithography
- Stainless Steel Screen 200 mesh, 45 °angle
- Wire Diameter 40.64 μm
- Emulsion Thicknesses from 12.5 to 50.8 μm
- Glass Frit Paste FX11-036



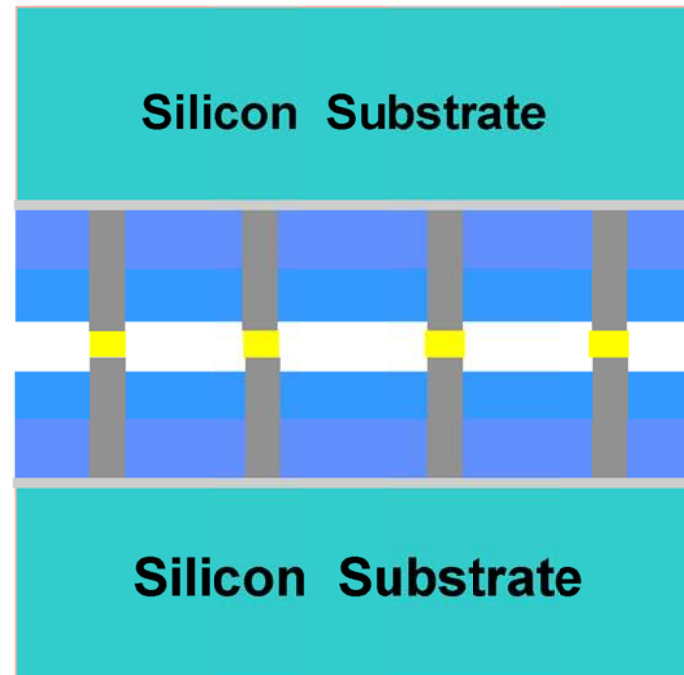
GLASS FRIT BONDING

- Glass Frit has Refractory Fillers to Modify CTE
- 30 μm -thick Glass Frit on Si
- Bonding of Si to Pyrex at 450 °C for 10 min and 1000 N
- Good Coverage Over Topologies





THERMOCOMPRESSION GOLD TO GOLD BONDING



- Provides a conductive interconnection of two substrates
- More difficult process because the gold does not compress more than a few thousand Angstroms

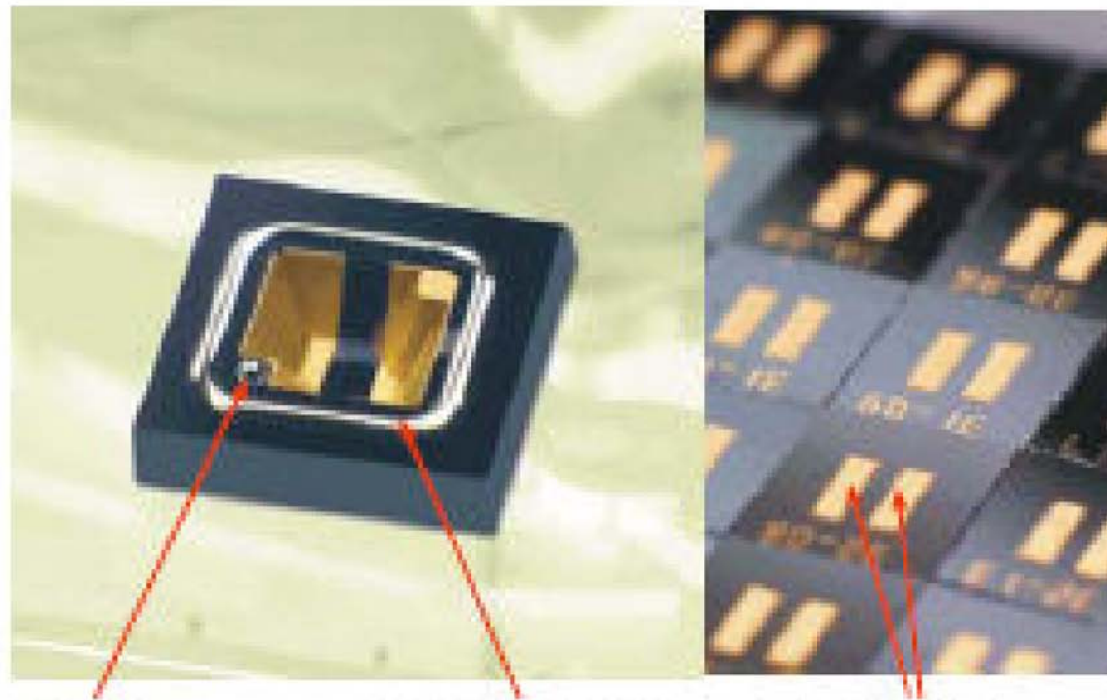


EPOXY BONDING

- **Low Temperature, 150 C or less**
- **Strong, shear 7-15 MPa shear**
- **Can be electrically conductive or insulating**
- **Easy to integrate as a last process step**
- **Shellcase is using epoxy bonding commercially**
<http://www.shellcase.co.il>



SOLDER BONDING



bump

sealing ring

SMD pads

Figure 1 HyCap® cavity side with AuSn sealing ring and bump (left) and HyCap® back side after assembly (right)

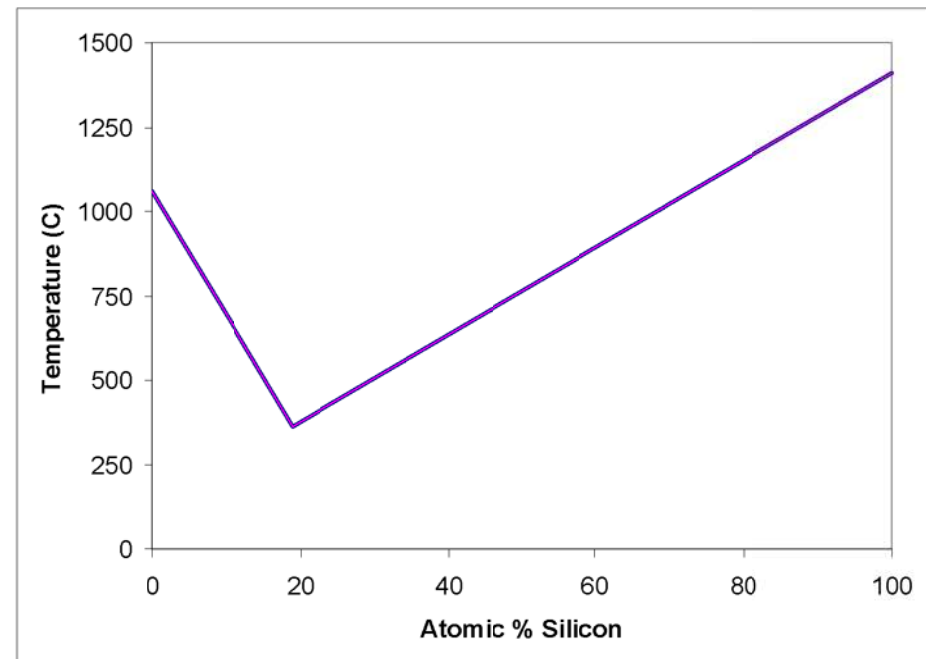
Courtesy of Hymite
www.hymite.com

- Works with most types of solders



AU:SI EUTECTIC BONDING

- Gold and silicon liquefy into each other
- Sensitive to chemical contamination
- Sensitive to temperature that are too high or low
- Bonding process often require scrubbing
- Sensitive to oxygen in atmosphere
- Sensitive to time at temperature
- Very good thermal conductivity
- Good electrical conductivity
- Good mechanical strength





OUTLINE

- **Integrated Package**
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- **MEMS Packaging Issues**

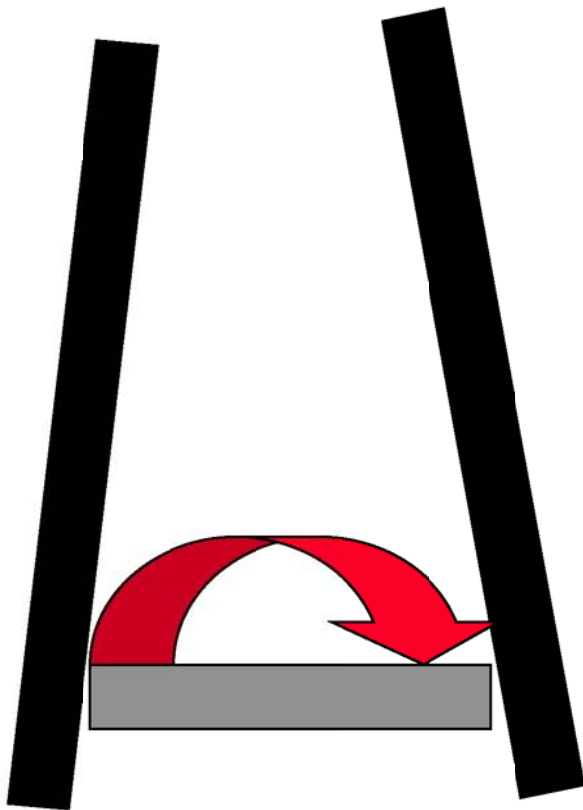


MEMS SPECIFIC PACKAGING

- **There are a couple of packaging techniques that are MEMS specific**
- **However, most MEMS packaging is borrowed from other sources**
- **However, the considerations of particles, mechanical damage, non standard films, outgassing, and stiction, are unique to MEMS**

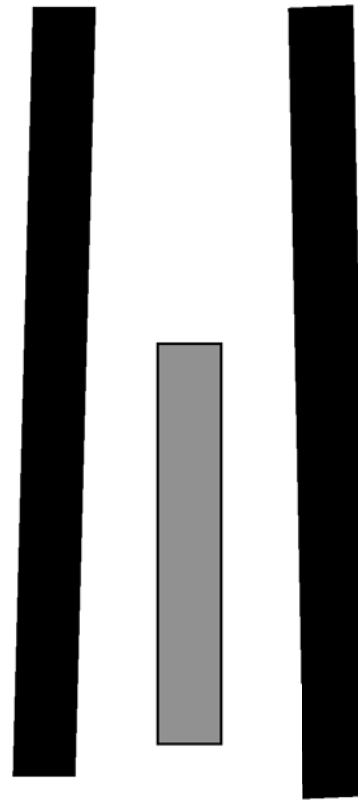


MEMS HANDILING WITH TWEEZERS

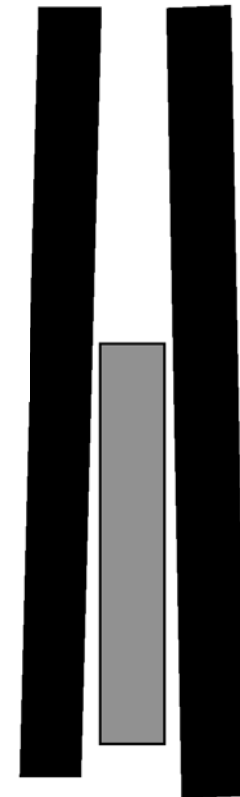


Not a good mass production technique, but works OK for prototypes

1



2



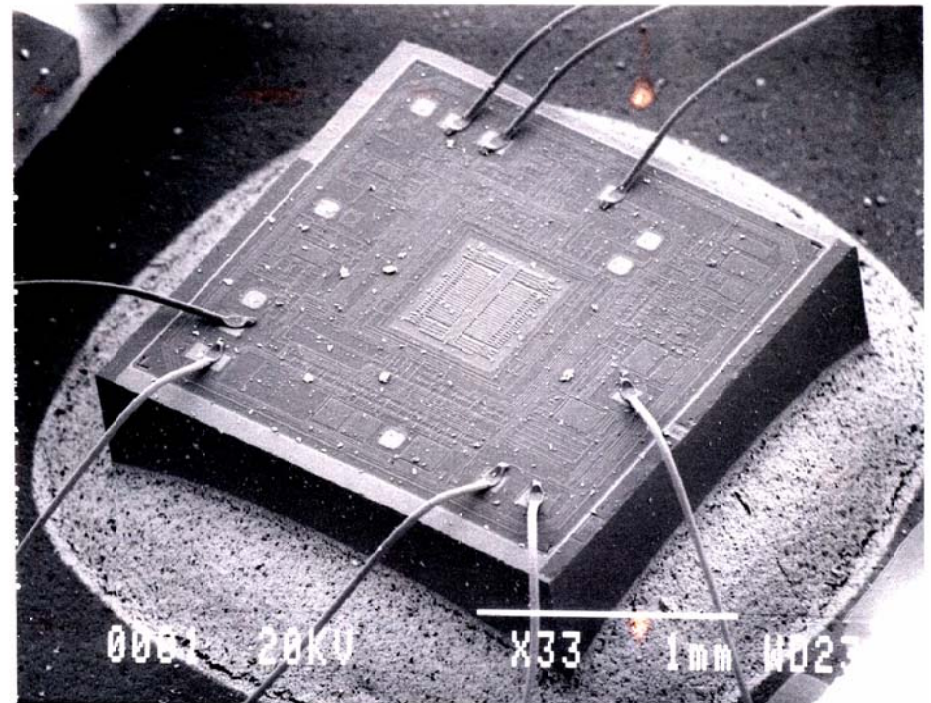
3

Your device is smashed



MEMS DIE ATTACH

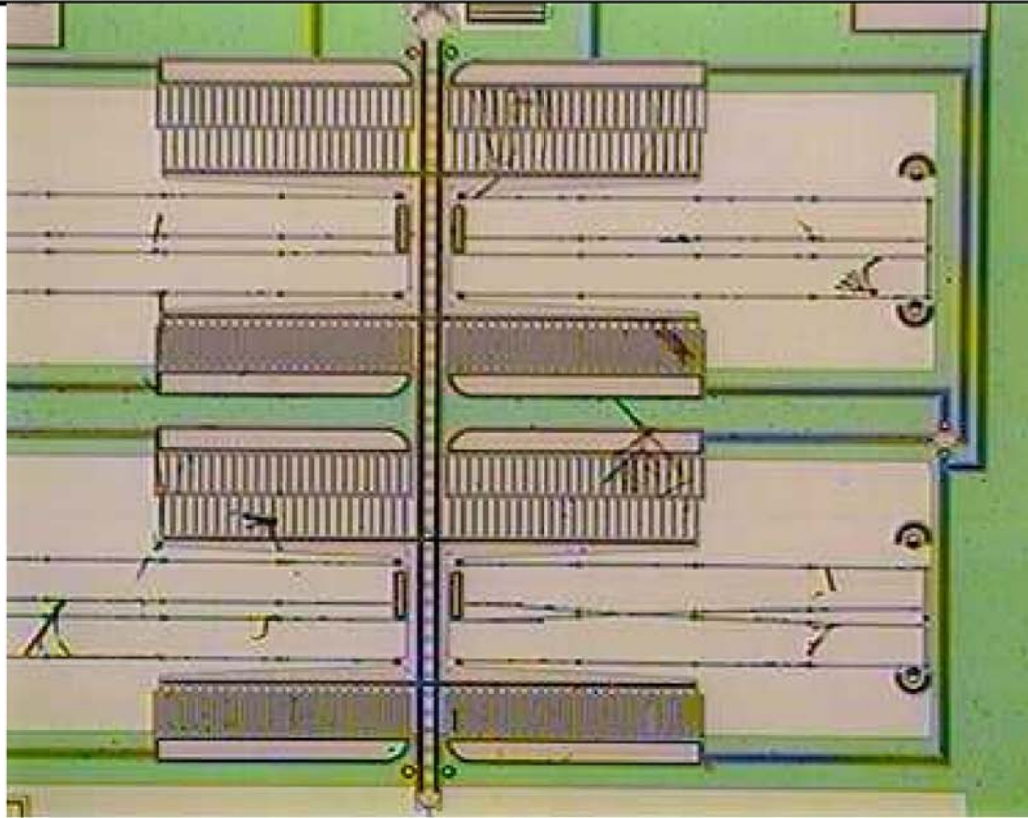
- Outgassing and temperature are concerns
- Solder — Eutectic Au/Si (370°C), Au/Sn (280°C)
- Epoxies (70-80% Ag, silica filled)
 - Typical cure 150°C, 30-60 minutes



Epoxy Die Attach
Analog Devices ADXL-50



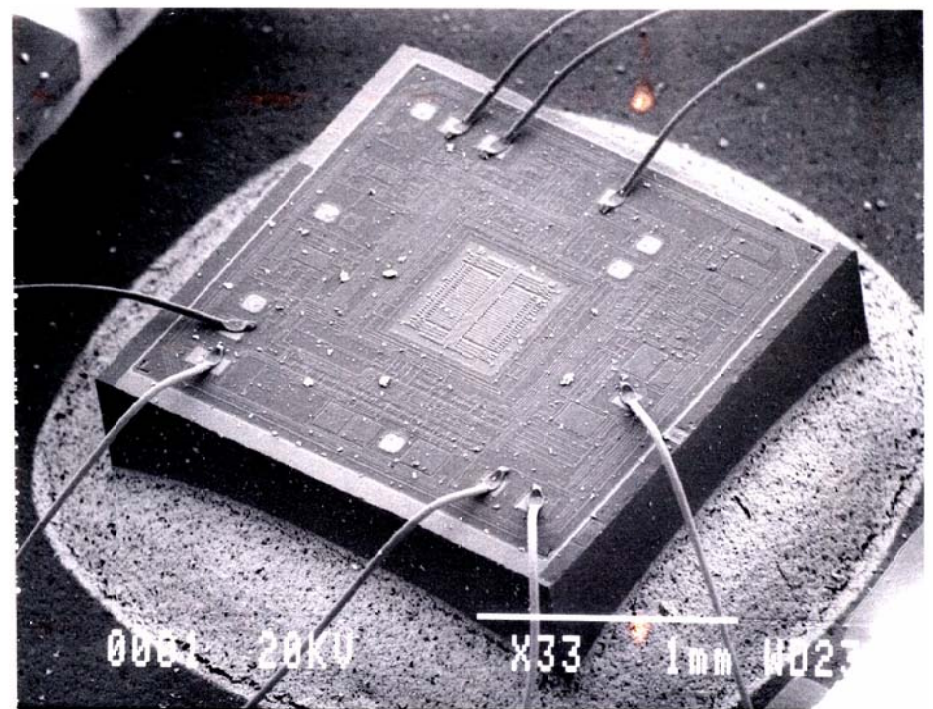
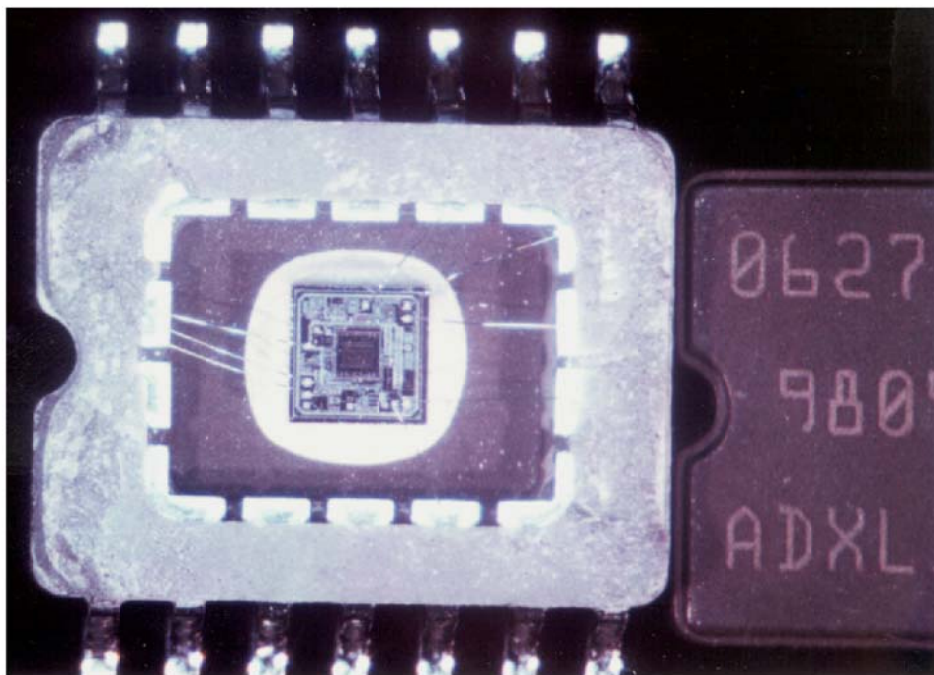
PARTICLES AND MEMS



- **Unlike ICs, MEMS with moving parts must be packaged in a particle free environment**



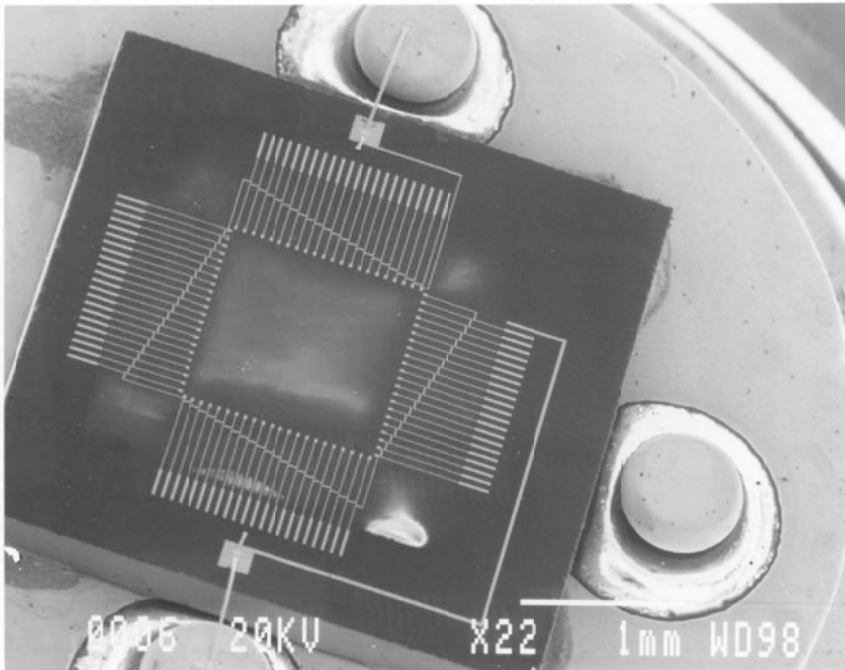
PACKAGED SURFACE MICROMACHINE



- **Hermetic ceramic package**



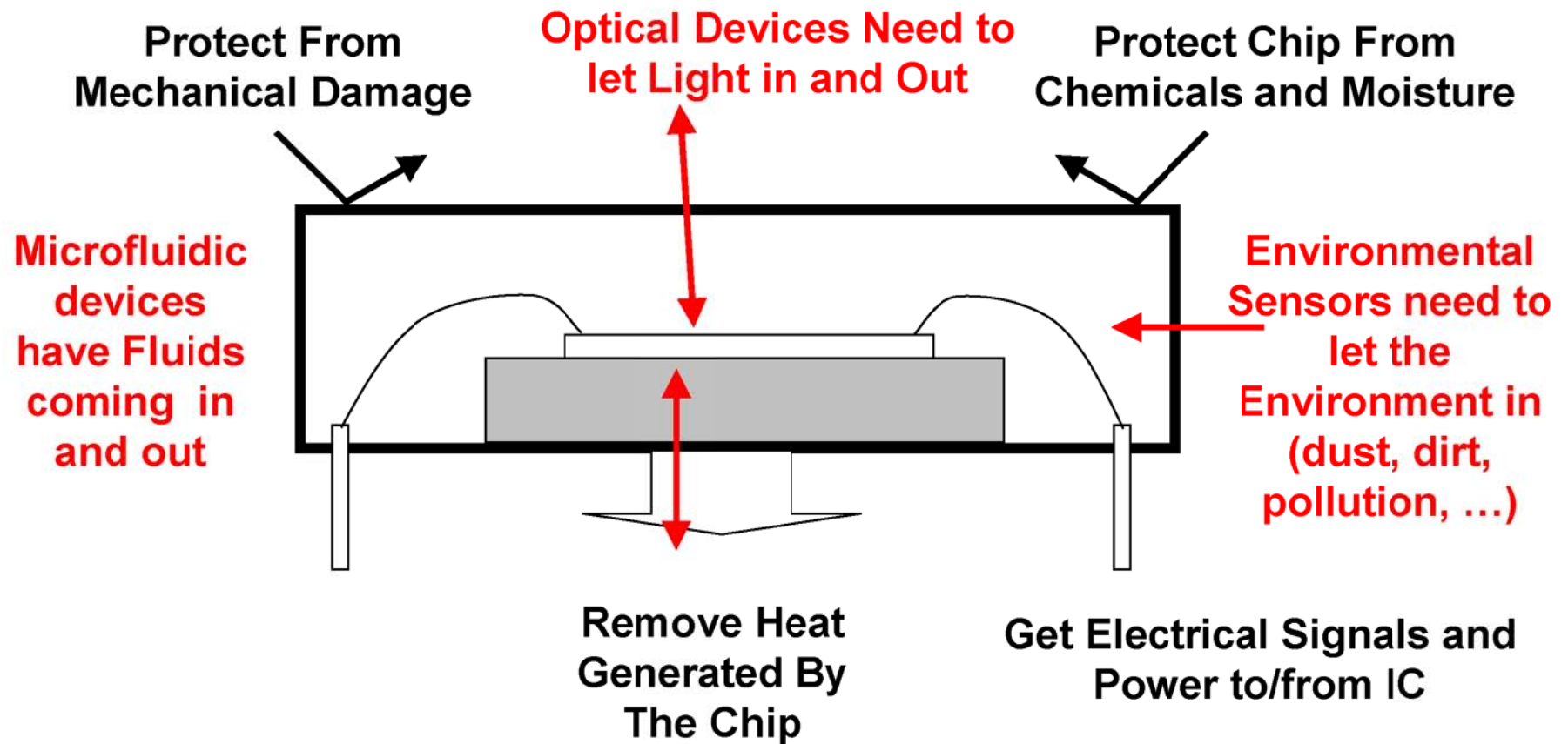
MEMS PACKAGING EXAMPLE



- **S150 bulk micromachined infrared detector from Dexter Research Center**
- **Welded TO can package with optical window**
- **Proprietary infrared absorbing layer (black)**



GOAL OF MEMS PACKAGING



Don't Limit Performance

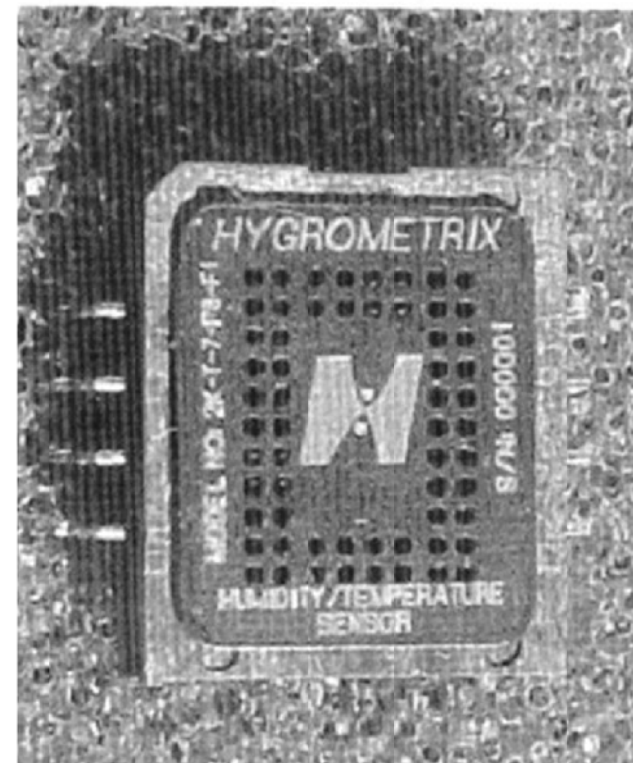
Low Cost

- So how do we get chemicals in?



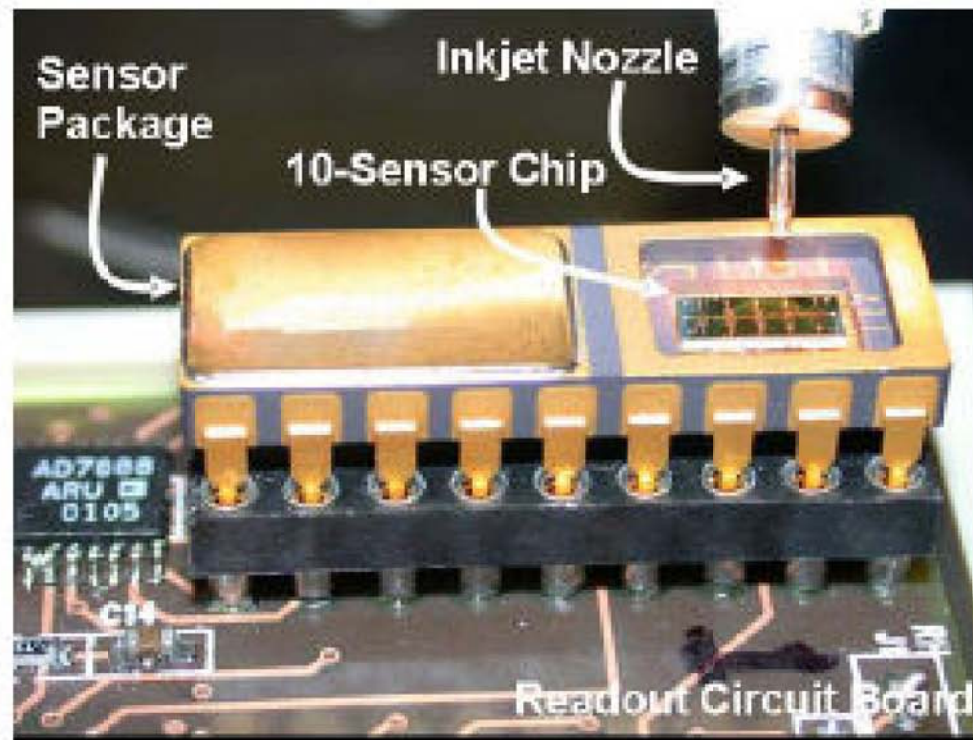
ENCAPSULATION

- Most sensors do not use fancy encapsulation schemes to protect them from the environment
- The Hygrometrix humidity sensor uses holes in the package lid





SEACOAST SENSOR



- Sensor is protected by a fine screen
- Readout chip is hermetically sealed

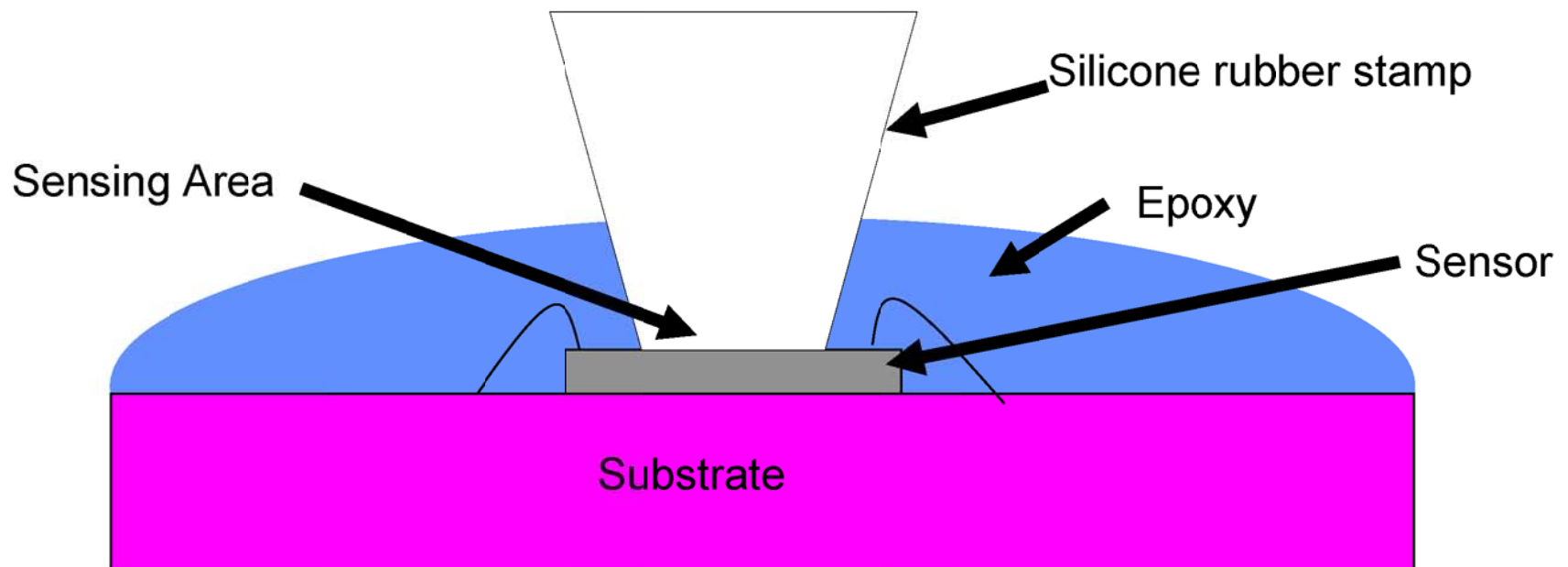


ENCAPSULATION

- **Many readout circuits in chemical sensors are protected**
- **Especially in liquid sensor applications these encapsulates must have very good adhesion**
 - **2 part epoxies must have no bubbles (vacuum aeration)**
 - **Silicone rubbers**
 - **Moisture resistant**
 - **Good adhesion**
 - **Parylene (thermoplastic polymer)**
 - **Vacuum deposited**
 - **Conformal coating**
 - **Wafer bonding**
 - **Hermetic and expensive and perhaps high temperature**



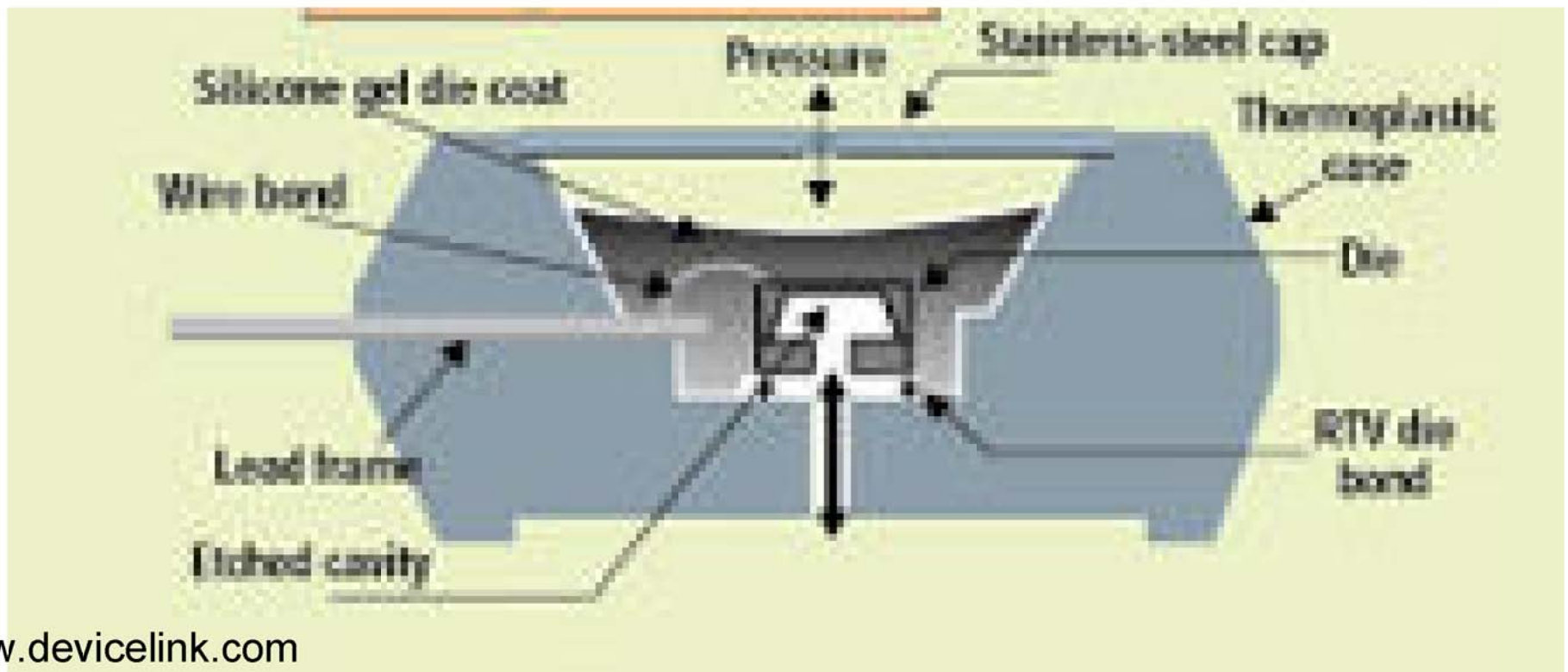
STAMP ENCAPSULATION METHOD





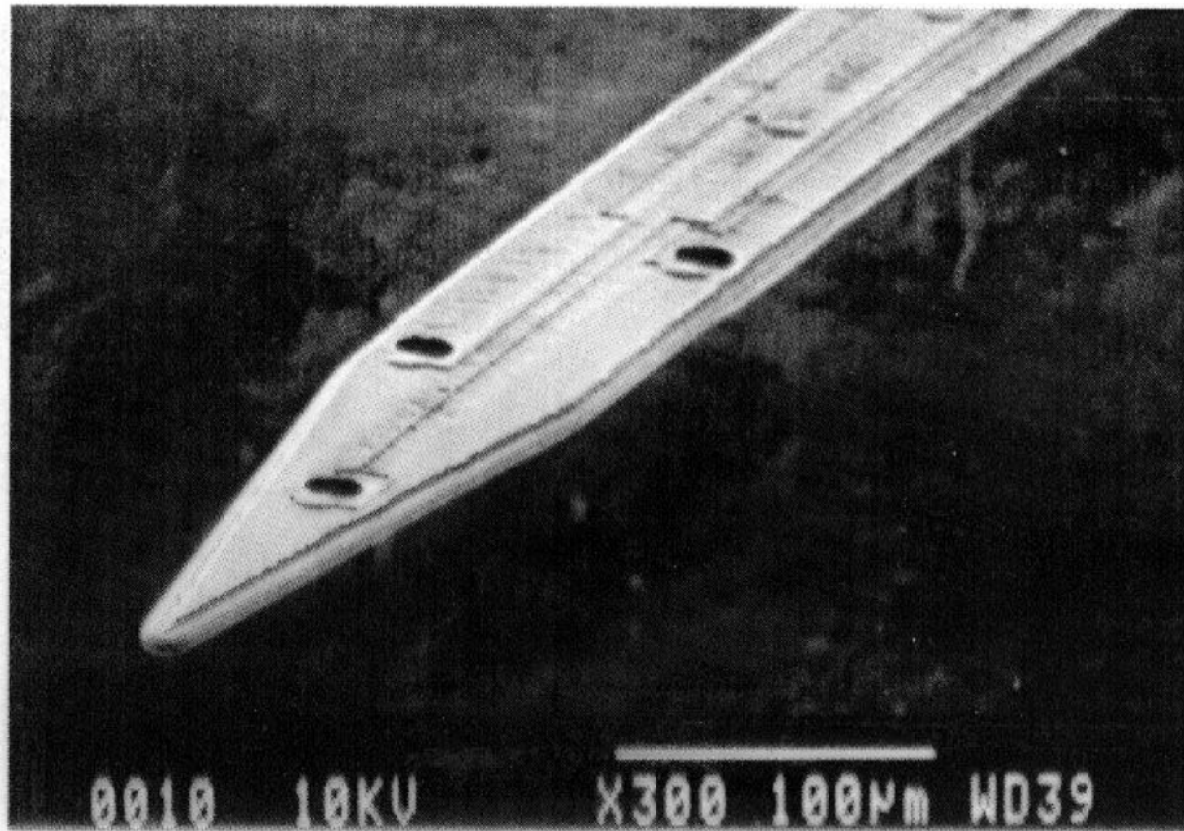
PACKAGING OF AN AUTOMOTIVE PRESSURE SENSOR

- Sensor element is isolated from the medium
- Other types of pressure sensors are bonded or fabricated on the backside of the steel cap





SOME DEVICES ARE THEIR OWN PACKAGE



Neural Probe

**JK Chen, the University of Michigan, now with the
University of New Mexico**



MEMS PACKAGING CONCLUSIONS

- **No general solution typically custom**
- **Based on IC packaging**
- **Surface micromachines require special handling, surface films, and protection from particles**
- **The main issue with MEMS packaging is that it is application specific**
- **In contrast, IC packaging is not application specific and has 40 years of experience behind it.**



REFERENCES

- **MEMS Packaging** Tai-Ran Hsu, ed. Chapters 2 and 3
- **Microsystem Packaging** by R. Tummala
- **Plasma activated fusion bonding information at**
 - **www.suss.com**
 - **www.ziptronix.com**
- **Other vendors include**
 - **<http://www.evgroup.com/>**



ACKNOWLEDGEMENTS

- **Much of this information came from a course I taught at the University of New Mexico on packaging**
- **Other information came from Dr. Ted Dellin at Sandia who co-taught an internal Sandia packaging course with me in 2004 and 2006**
- **Special thanks to Jon Custer, Helena Chan, Brian Stark, JK Chen, Lauren Rohwer, and Melissa Collins whose work is represented here and who provided some of the pictures**